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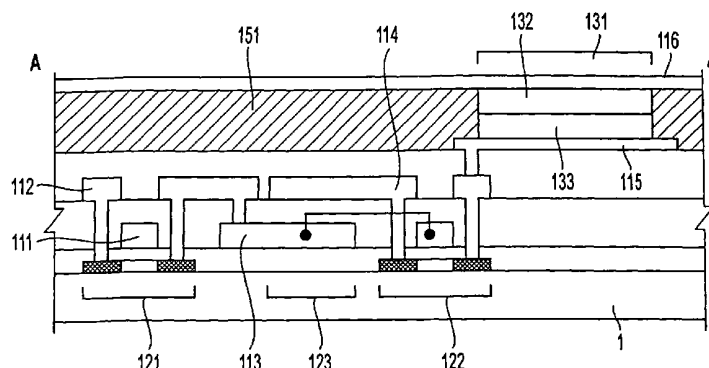
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(57) **ABSTRACT**

A method for producing an organic EL display device is disclosed. The display device comprises a substrate, a transistor disposed on the substrate, a flattened inter-layer insulation film covering the transistor, a pixel electrode, and an organic EL layer.

13 Claims, 10 Drawing Sheets



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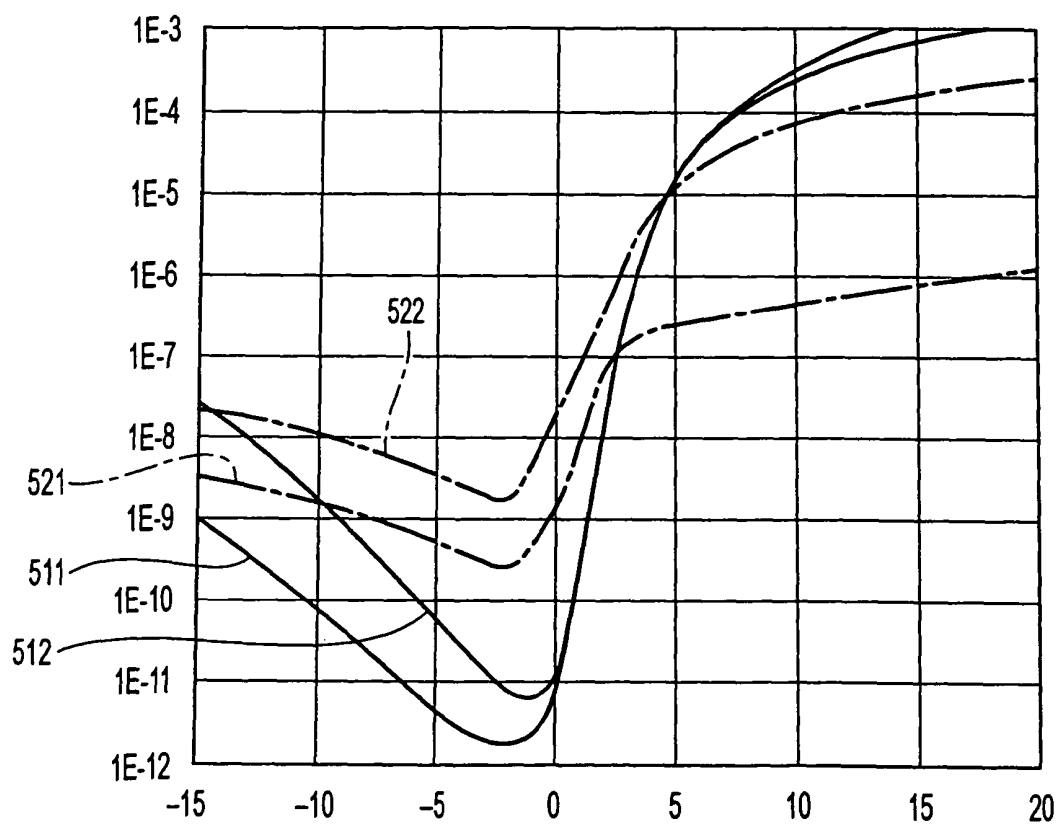
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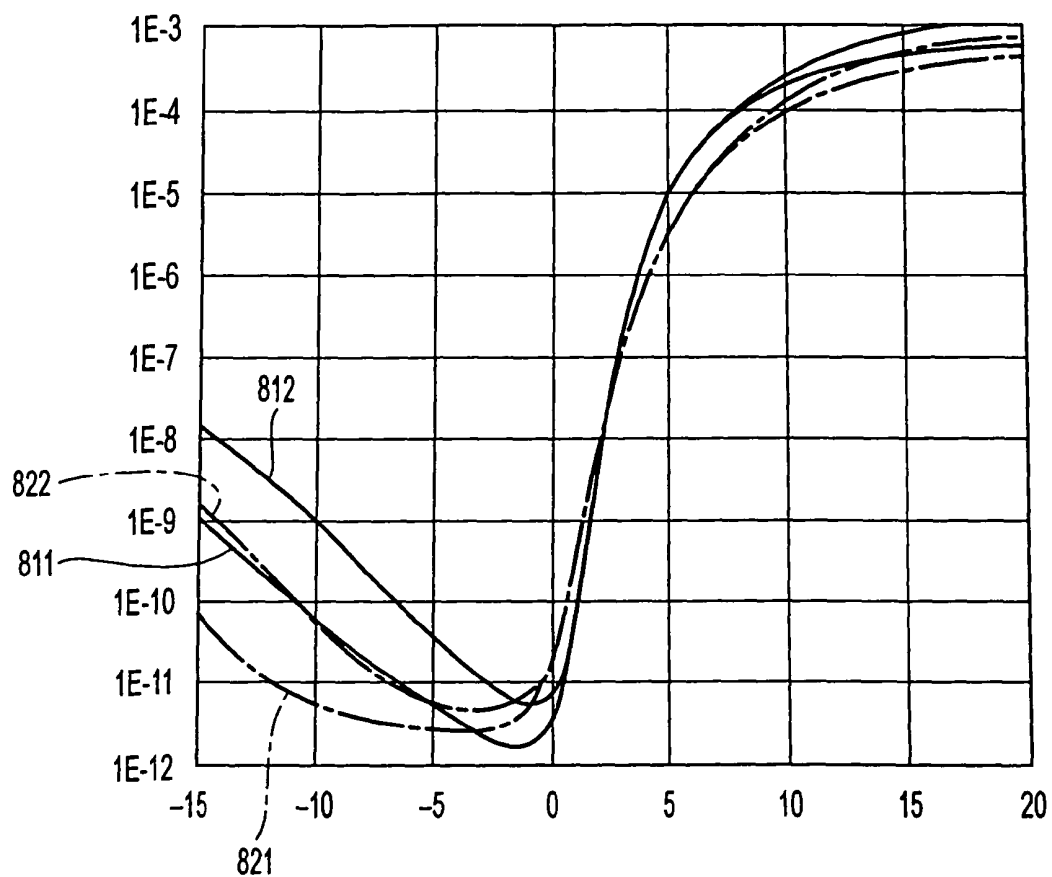
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**FIG. 12**

**FIG. 13**

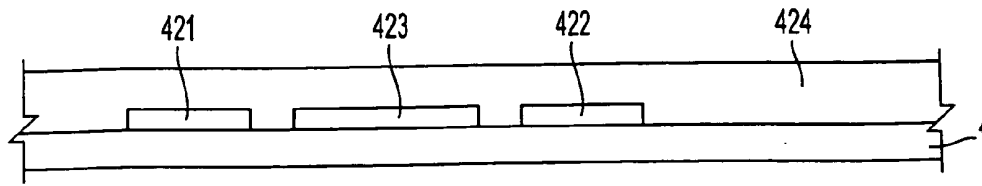


FIG. 14(a)

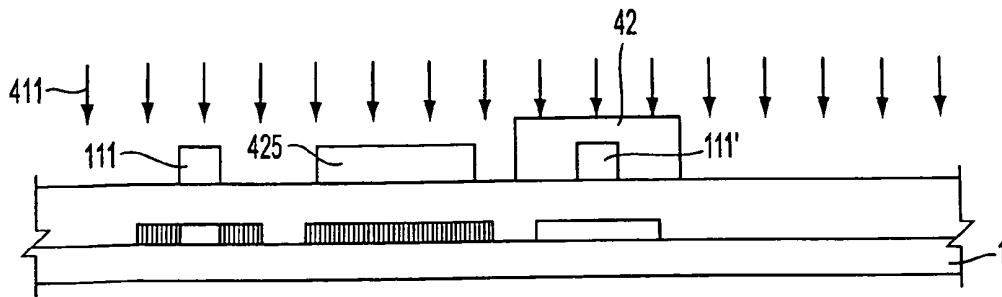


FIG. 14(b)

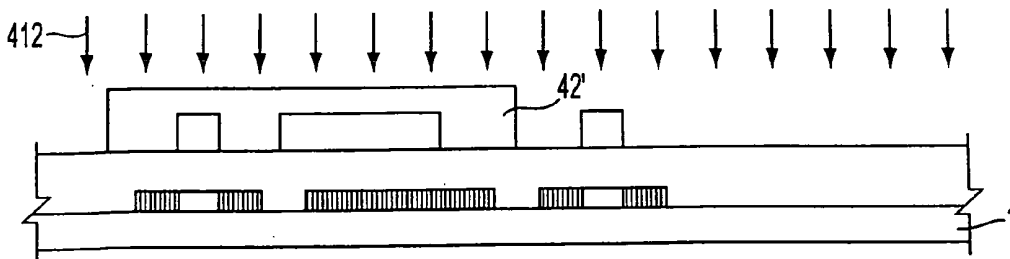


FIG. 14(c)

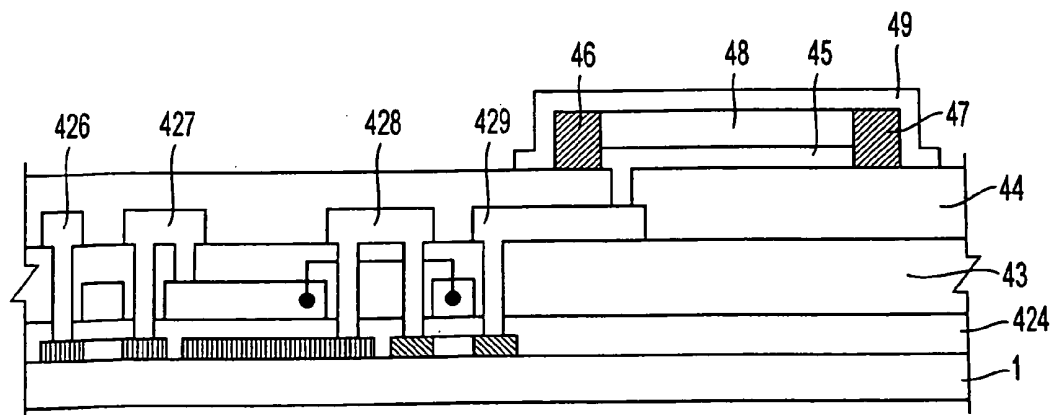


FIG. 14(d)

CURRENT-DRIVEN LIGHT-EMITTING DISPLAY APPARATUS AND METHOD OF PRODUCING THE SAME

This is a Continuation of application Ser. No. 10/465,878 filed Jun. 20, 2003, which in turn is a Divisional of application Ser. No. 10/224,412 filed Aug. 21, 2002, which in turn is a Divisional of application Ser. No. 09/155,644 filed Oct. 2, 1998, which in turn claims priority of Japanese Application No. 09-032474 filed Feb. 17, 1997 and Japanese Application No. 09-066046 filed Mar. 19, 1997. The disclosure of the prior applications is hereby incorporated by reference herein in its entirety.

BACKGROUND OF THE INVENTION

1. Field of Invention

The invention relates to a display apparatus in which a current-driven light-emitting device, such as an organic electro luminescence (hereinafter referred to as "EL") display device, are driven by using thin-film transistors. More particularly, the invention relates to a current-driven light-emitting display apparatus driven by thin-film-transistors, which realizes the suppression of deterioration with time, and to a method of producing the same.

2. Description of Related Art

The inventor of this invention carefully examined organic EL display devices driven by thin-film transistors, and ascertained the following facts.

(1) In an organic EL display device driven by thin-film transistors, since the organic EL display device is a direct-current device, direct current also runs through thin-film transistors, which are connected in series to the EL device, for the purpose of controlling it.

(2) Thin-film transistors are classified into an n-channel type and a p-channel type. These types differ extremely in the manner in which deterioration with time occurs.

Accordingly, an object of the present invention is to suppress the deterioration with time of thin-film transistors in a current luminescent device driven by the thin-film transistors.

SUMMARY OF THE INVENTION

(1) In the present invention, there is provided a current-driven light-emitting display apparatus comprising a plurality of scanning lines and a plurality of data lines, thin-film transistors and current luminescent devices being formed in positions corresponding to each of the intersections of the scanning lines and the data lines, wherein at least one of the thin-film transistors is a p-channel type thin-film transistor.

It is possible to suppress the deterioration with time of a thin-film transistor with this apparatus.

(2) In the present invention, there is provided a current-driven light-emitting display apparatus in which a plurality of scanning lines a plurality of data lines, common electrodes, and opposite electrodes are formed, with first thin-film transistors being formed in positions corresponding to the intersections of the scanning lines and the data lines, second thin-film transistors, holding capacitors, pixel electrodes, and current luminescent elements, the first thin-film transistors controlling conductivity between the data lines and the holding capacitors by the potentials of the scanning lines, the second thin-film transistors controlling conductivity between the common electrodes and the pixel electrodes by the potentials of the holding capacitors, to thereby control the current which flows through the current luminescent elements pro-

vided between the pixel electrodes and the opposite electrodes wherein the second thin-film transistors are p-channel type thin-film transistors.

(3) In the present invention, there is provided a current-driven light-emitting display apparatus according to (1) or (2), further comprising a driving circuit for driving the current luminescent element, the driving circuit is comprised of the plurality of scanning lines, the plurality of data lines, the thin-film transistors, and the current luminescent elements, which are disposed on the substrate, wherein the p-channel type thin-film transistors are formed in the same step as the thin-film transistors in the driving circuits.

(4) In the current-driven light-emitting display apparatus according to any of (1) or (3), the thin-film transistors are polysilicon thin-film transistors.

(5) The invention provides a current-driven light-emitting display apparatus according to (3), wherein the drive circuits comprise complementary type thin-film transistors, the first thin-film transistors are formed in the same step as n-channel type thin-film transistors in the driving circuits, and the second thin-film transistors are formed in the same step as the p-channel type thin-film transistors in the driving circuits.

According to (5), it is possible to provide a current-driven light-emitting display apparatus, which exhibits high performance with no deterioration with time, without increasing the number of steps for producing the apparatus.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a block diagram of the basic structure of a display to which the present invention is applied;

FIG. 2 is an equivalent circuit diagram of a display device equipped with thin-film transistors according to a first embodiment of the present invention;

FIG. 3 is a drive voltage diagram of the display device equipped with thin-film transistors according to the first embodiment of the present invention;

FIG. 4 is a current-voltage characteristic chart of a current-thin-film transistor according to the first embodiment of the present invention;

FIG. 5 is a current-voltage characteristic chart of an organic EL display device according to the first embodiment of the present invention;

FIG. 6(a) is a sectional view of an organic display EL device equipped with thin-film transistors according to the first embodiment of the invention, and FIG. 6(b) is a plan view of an organic display EL device according to the first embodiment of the present invention;

FIG. 7 is an equivalent circuit diagram of an organic EL display device equipped with thin-film transistors used in a second embodiment of the present invention;

FIG. 8 is a drive-voltage diagram of an organic EL display device equipped with thin-film transistors according to the second embodiment of the present invention;

FIG. 9 is a current-voltage characteristic chart of a current-thin-film transistor according to the second embodiment of the present invention;

FIG. 10 is a current-voltage characteristic chart of an organic EL display device according to the second embodiment of the present invention;

FIG. 11(a) is a sectional view of an organic EL display device equipped with thin-film transistors according to the second embodiment of the present invention, and FIG. 11(b) is a plan view of an organic EL display device equipped with thin-film transistors according to the second embodiment of the present invention;

FIG. 12 is a chart showing the deterioration with time of an n-channel type thin-film transistor;

FIG. 13 is a chart showing the deterioration with time of a p-channel type thin-film transistor; and

FIG. 14(a)-(d) are flow diagrams of the process for producing a thin-film-transistor-drive organic EL display device according to the present invention.

DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS

The General Structure of an Organic EL Display Device

Referring to the drawings, the preferred embodiments of the present invention will be described.

As shown in FIG. 1, the center region of a substrate 1 constitutes a display part. In the outer periphery of the transparent substrate 1, at the top side of the drawing, a data-side drive circuit 3, which outputs image signals to data lines 112, is arranged, and at the left side of the drawing, a scanning-side drive circuit 4, which outputs scanning signals to scanning lines 111, is arranged. In these drive circuits 3 and 4, n-type thin-film transistors and p-type thin-film transistors form complementary type TFTs. These complementary type thin-film transistors are included in shift register circuits, level shift circuits, analog switch circuits, etc.

Arranged on the transparent substrate 1 are a plurality of scanning lines 111, and a plurality of data lines 112 extending in a direction perpendicular to the direction in which the scanning lines extend. The intersections of these data lines 112 and scanning lines 111 constitute pixels 7 in the form of a matrix.

Formed in each of these pixels 7 is a first thin-film transistor (hereinafter referred to as "a switching thin-film transistor") 121, in which scanning signals are supplied to a gate electrode 21 (a first gate electrode) through the scanning line 111. One end of the source/drain region of the switching thin-film transistor 121 is electrically connected to a data line 112, while the other end of the source/drain region is electrically connected to a potential holding electrode 113. In addition, a common line 114 is disposed in parallel to the scanning line 111. Holding capacitor 123 is formed between the common line 114 and the potential holding electrode 113. The common line is maintained at a controlled potential. Accordingly, when the switching thin-film transistor 121 is turned ON through the selection by a scanning signal, the image signal from the data line 112 is written to the holding capacitor 123 through the switching thin-film transistor.

The potential holding electrode 113 is electrically connected to the gate electrode of second thin-film transistor 122 (hereinafter referred to as "a current-thin-film transistor"). The one end of the source/drain region of the current-thin-film transistor 122 is electrically connected to a common line 114, while, the other end of the source/drain region is electrically connected to one electrode 115 of a luminescent element 131. When the current-thin-film transistor 122 is turned ON, the current of the common line 114 flows to the luminescent element 131 of such as an organic EL display device through the current-thin-film transistor 122, so that the luminescent element 131 emits light. Further, although one electrode of the holding capacitor is connected to a common line 114 in this arrangement, it is also possible for it to be connected to a capacitance line being provided separately, instead of being connected to the common line 114. Alternatively, one electrode of the holding capacitor may be connected to an adjacent gate line.

(First Embodiment)

FIG. 2 is a block diagram of an organic EL display device equipped with thin-film transistors, according to a first embodiment of the present invention. FIG. 3 is a drive voltage diagram of an organic EL display device with thin-film transistors, according to the first embodiment of the present invention. FIG. 4 is a current-voltage characteristic diagram of a current-thin-film transistor according to the first embodiment of the present invention. FIG. 5 is a current-voltage characteristic chart of an organic EL display device, according to the first embodiment of the present invention.

In FIG. 2, there are shown a scanning line 111, a data line 112, a holding electrode 113, a common line 114, a pixel electrode formed of Al 115, an opposite electrode formed of ITO 116, a switching thin-film transistor 121, an n-channel type current-thin-film transistor 122, a holding capacitor 123, an organic EL display element 131 (hereinafter referred to as "a forward oriented organic EL display device") which is caused to emit light by the current flowing to the pixel electrode 115 from the opposite electrode 116, and the current directions of the organic EL display device 131 and 141.

In FIG. 3, there are shown a scanning potential 211, a signal potential 212, a holding potential 213, a common potential 214, a pixel potential 215, and a counter potential 216. FIG. 3, only a part of each potential is shown to illustrate the respective potential relationships. The potential of the scanning line 111 corresponds to the scanning potential 211; the potential of the data line 112 corresponds to the signal potential 212; the potential of the holding electrode 113 corresponds to the holding potential 213; the potential of the common line 114 corresponds to the common potential 214; the potential of the pixel electrode 115 formed of Al corresponds to the pixel potential 215; and the potential of the opposite electrode 116 formed of ITO (Indium Tin Oxide) corresponds to the counter potential 216. FIG. 3 shows each signal potential schematically and partially.

Numeral 221 indicates a period in which a pixel is in the display-state, wherein current flows into the forward oriented organic EL display element 131, so that it emits light, and numeral 222 indicates a period in which the pixel is in the non-display state, wherein current does not flow into the forward oriented organic EL display element 131, so that it does not emit light.

Referring to FIG. 4, a curve 31 indicates the current-voltage characteristic of the n-channel type current-thin-film transistor 122 as observed when the drain voltage is 4V, and a curve 32 indicates the current-voltage characteristic of the n-channel type current-thin-film transistor 122 as observed when the drain voltage is 8V. Regarding either drain voltage, the following facts can be seen. When the gate voltage is low, the n-channel type current-thin-film transistor 122 is turned OFF and a small amount of drain current flows demonstrating a high source/drain resistance. When the gate voltage is high, the n-channel type current-thin-film transistor 122 is turned ON and a large amount of drain current flows demonstrating a low source/drain resistance.

In FIG. 5, numeral 4 indicates the current-voltage characteristic of the forward oriented organic EL display element 131. Here, the voltage represents the counter potential 216 against the pixel potential 215, and the current represents the current which flows to the pixel electrode 115 from the opposite electrode 116. The forward oriented organic EL display element 131 is OFF when the voltage is not higher than a certain threshold voltage; the resistance is high and allows no current to flow, so that the device does not emit light. The device is ON when the voltage is over a certain threshold

voltage, and the resistance is low and allows current to flow, so that the device emits light. In this case, the threshold voltage is approximately 2V.

The operation of an organic EL display device equipped with the thin-film transistors of this embodiment will be described with reference to FIG. 2, FIG. 3, FIG. 4, and FIG. 5.

The switching thin-film transistor **121** controls the conductivity between the data line **112** and the holding electrode **113** by means of the potential of the scanning line **111**. In other words, the scanning potential **211** controls the conductivity between the signal potential **212** and the holding potential **213**. While in this example, the switching thin-film transistor **121** is an n-channel type thin-film transistor, a p-channel type thin-film transistor is also applicable.

For the period **221** in which the pixel is in the display-state, the signal potential **212** is high, and the holding potential **213** is retained at a high level. For the period **222** in which the pixel is in the non-display state, the signal potential **212** is low, and the holding potential **213** is retained at a low level.

The n-channel type current-thin-film transistor **122** has the characteristic as shown in FIG. 3 and controls the conductivity between the common line **114** and the pixel electrode **115** by means of the potential of the holding electrode **113**. In other words, the holding potential **213** controls the conductivity between the common potential **214** and the pixel potential **222**. For the period **221** in which the pixel is in the display-state, the holding potential **213** is high, so that the common line **114** is electrically connected to the pixel electrode **115**. For the period **222** in which the pixel is in the non-display state, the holding potential **213** is low, so that the common line **114** is disconnected from the pixel electrode **115**.

The organic EL display element **131** has the characteristic as shown in FIG. 5. For the period **221** in which the pixel is in the display-state, the current flows between the pixel electrode **115** and the opposite electrode **116**, so that the organic EL display element **131** emits light.

For the period **222** in which the pixel is in the non-display state, no current flows, so that the device does not emit light.

FIG. 6(a) is a sectional view of a thin-film transistor organic EL display device (1 pixel) according to an embodiment of the present invention. FIG. 6(b) is a plan view of a thin-film transistor organic EL display device (1 pixel) according to an embodiment of the present invention. The section taken along the line A-A' of FIG. 6(a) corresponds to the section taken along the line A-A' of FIG. 6(b).

In FIG. 6(a), numeral **132** indicates a hole injection layer, numeral **133** indicates an organic EL layer, and numeral **151** indicates a resist.

In this example, the switching thin-film transistor **121** and the n-channel type current-thin-film transistor **122** adopt the structure and the process ordinarily used for a low-temperature polysilicon thin-film transistor, which are used for thin-film transistor liquid crystal display devices, i.e., a top-gate structure and a process conducted in the condition that the maximum temperature is 600° C. or less. However, other structures and processes are also applicable.

The forward oriented organic EL display element **131** is formed by the pixel electrode **115** formed of Al, the opposite electrode **116** formed of ITO, the hole injection layer **132**, and the organic EL layer **133**. In the forward oriented organic EL display element **131**, the direction of current of the organic EL display device, indicated at **141**, can be set from the opposite electrode **116** formed of ITO to the pixel electrode **115** formed of Al. Further, the structure of the organic EL display device is not restricted to the one used here. Other structures are also applicable, as long as the direction of current of the

organic EL display device, indicated at **141**, can be set to the direction from the opposite electrode to pixel electrode.

Here, the hole injection layer **132** and the organic EL layer **133** are formed by an ink-jet printing method, employing the resist **151** as a separating structure between the pixels, and the opposite electrode **116** formed of ITO is formed by a sputtering method, yet other methods are also applicable.

In this embodiment, the common potential **214** is lower than the counter potential **216**, and the current-thin-film transistor is the n-channel type current-thin-film transistor **122**.

In the period **221** in which the pixel is in the display-state, the n-channel type current-thin-film transistor **122** is ON. The current which flows through the forward oriented organic EL display element **131**, i.e., the ON-current of the n-channel type current-thin-film transistor **122** depends on the gate voltage, as shown in FIG. 4. Here, the term "gate voltage" means the potential difference between the holding potential **213** and the lower one of the common potential **214** and the pixel potential **215**. In this embodiment, the common potential **214** is lower than the pixel potential **215**, so that the gate voltage indicates the potential difference between the holding potential **213** and the common potential **214**. The potential difference can be sufficiently large, so that a sufficiently large amount of ON-current is obtainable. The ON-current of the n-channel type current-thin-film transistor **122** also depends on the drain voltage. However, this does not affect the above situation.

Conversely, in order to obtain a necessary amount of ON-current, the holding potential **213** can be made lower, and the amplitude of the signal potential **212** and therefore the amplitude of the scanning potential **211** can be decreased. In other words, in the switching thin-film transistor **121** and the n-channel type current-thin-film transistor **122**, a decrease in drive voltage can be achieved without entailing any loss in image quality, abnormal operations, or a decrease in the frequency enabling them to operate.

Further, in the embodiment of the present invention, the signal potential **212** for the pixel to be in the display-state is lower than the counter potential **216**.

As stated above, in the period **221** in which the pixel is in the display-state, the ON-current of the n-channel type current-thin-film transistor **122** depends on the potential difference between the holding potential **213** and the common potential **214**, but not directly on the potential difference between the holding potential **213** and the counter potential **216**. Thus, the holding potential **213**, i.e., the signal potential **212** for the pixel to be in the display-state, can be made lower than the counter potential **216**, and therefore, the amplitude of the signal potential **212** and the amplitude of the scanning potential **211** can be decreased, while retaining a sufficiently large ON-current in the n-channel type current-thin-film transistor **122**. That is, in the switching thin-film transistor **121** and the n-channel type current-thin-film transistor **122**, a decrease in drive voltage can be accomplished without entailing any loss in image quality, abnormal operations, and a decrease in the frequency enabling them to operate.

Moreover, in this embodiment, the signal potential **212** for the pixel to be in the non-display-state is higher than the common potential **214**.

In the period **222** in which the pixel is in the non-display-state, when the signal potential **212** becomes slightly higher than the common potential **214**, the n-channel type current-thin-film transistor **122** is not completely turned OFF. However, the source/drain resistance of the n-channel type current-thin-film transistor **122** becomes considerably higher, as shown in FIG. 4. Thus, the pixel potential **215**, which is determined by dividing the common potential **214** and the

counter potential **216** by the values of the resistance of the n-channel type current-thin-film transistor **122** and the resistance of the forward oriented organic EL display element **131**, becomes a potential close to the counter potential **216**.

The voltage which is applied to the forward oriented organic EL display element **131** is the potential difference between the pixel potential **215** and the counter potential **216**. As shown in FIG. 5, the forward oriented organic EL display element **131** is turned OFF when the voltage is not higher than a certain threshold voltage, when no current flows, so that the display device does not emit light. Namely, the utilization of a threshold potential of the forward oriented organic EL display element **131** makes it possible for the forward oriented organic EL display element **131** not to emit light, even if the signal potential **212** is slightly higher than the common potential **214**, and the n-channel type current-thin-film transistor **122** is not completely turned OFF.

Here, the amplitude of the signal potential **212**, and therefore the amplitude of the scanning potential **211** can be decreased by making the signal potential **212** for the pixel to be in the non-display state to be higher than the common potential **214**. In other words, with regard to the switching thin-film transistor **121** and the n-channel type current-thin-film transistor **122**, a decrease in drive potential can be accomplished without entailing any loss of image quality, abnormal operations, or a decrease in the frequency enabling them to operate.

The operation of an organic EL display device equipped with the thin-film transistors of this embodiment is not as simple as described above; it operates under a more complicated relationship between voltage and current. However, the description above holds true approximately and qualitatively. (Second Embodiment)

FIG. 7 is an equivalent circuit diagram of an organic EL display device equipped with thin-film transistors, according to the second embodiment of the present invention. FIG. 8 is a drive voltage diagram of the organic EL display device with thin-film transistors, according to the second embodiment of the present invention. FIG. 9 is a current-voltage characteristic chart of the organic EL display device according to the second embodiment of the present invention.

In FIG. 7, there are shown a pixel electrode formed of ITO **615**, an opposite electrode formed of Al **616**, a p-channel type current-thin-film transistor **622**, and an organic EL display device **631** (hereinafter referred to as "a reverse oriented organic EL display device"), which is caused to emit light by the current flowing to the opposite electrode **616** from the pixel electrode **615**. Numeral **641** indicates the direction of the current of the organic EL display device. This direction is the reverse of that shown in FIG. 2. Except for this, this embodiment is the same as the above first embodiment shown in FIG. 2.

FIG. 8 is the same as FIG. 3 except that the level of each potential is different from that of FIG. 3.

In FIG. 9, a curve **81** indicates a current-voltage characteristic of a p-channel type current-thin-film transistor **622** as observed when the drain voltage is 4V. A curve **82** indicates a current-voltage characteristic of the p-channel type current-thin-film transistor **622** as observed when the drain voltage is 8V.

In FIG. 10, a curve **9** indicates a current-voltage characteristic of a reverse oriented organic EL display device **631**.

The organic EL display device equipped with the thin-film transistors of this embodiment operates in the same way as that of the first embodiment, except that the potential relationship regarding the current-thin-film transistor is reversed

due to the fact that the current-thin-film transistor is the p-channel type thin-film transistor **622**.

FIG. 11(a) is a sectional view of an organic EL display device (1 pixel) equipped with the thin-film transistors, according to the second embodiment of the present invention. FIG. 11(b) is a plan view of a thin-film transistor organic EL display device (1 pixel), according to the second embodiment of the present invention. The section taken along the line A-A' of FIG. 11(a) corresponds to the section taken along the line A-A' of FIG. 11(b).

FIG. 11(a) is the same as FIG. 6(a), except that it shows a hole injection layer **632** and an organic EL layer **633**.

The reverse oriented organic EL display device **631** is formed by means of the pixel electrode **615** formed of ITO, the opposite electrode **616** formed of Al, the hole injection layer **632**, and the organic EL layer **633**. In the reverse oriented organic EL display device **631**, the direction of current of the organic EL display device, indicated at **641**, can be set to the direction from the pixel electrode **615** formed of ITO to the opposite electrode **616** formed of Al.

In this embodiment, a common potential **714** is higher than a counter-potential **716**. Further, the current-thin-film transistor is the p-channel type current-thin-film transistor **622**.

In this embodiment, a signal potential **712** for the pixel to be in the display-state is higher than the counter potential **716**.

Furthermore, in this embodiment, the signal potential **712** for the pixel to be in the non-display-state is lower than the common potential **714**.

All of the effects of the thin-film transistor organic EL display device of this embodiment are also the same as those of the first embodiment, except that the potential relationship regarding the current-thin-film transistor is reversed due to the fact that the current-thin-film transistor is the p-channel type thin-film transistor **622**.

In this embodiment, the current-thin-film transistor **122** is a p-channel type thin-film transistor. This arrangement enables the deterioration with time of the current-thin-film transistor **122** to significantly decrease. Furthermore, the arrangement adopting a p-channel type polysilicon thin-film transistor enables the deterioration with time of the current-thin-film transistor **122** to decrease even further.

FIG. 14 is a diagram of a process of producing the current-driven light-emitting display apparatus equipped with the thin-film transistors, according to the embodiment of the present invention described above.

As shown in FIG. 14(a), an amorphous silicon layer with a thickness of 200 to 600 angstroms is deposited all over a substrate **1**, and the amorphous silicon layer is polycrystallized by laser annealing etc., to form a polycrystalline silicon layer. After this, patterning is performed on the polycrystalline silicon layer to form a silicon thin-film **421**, which serves as a source/drain channel region of the switching thin-film transistor **121**, a first electrode **423** of the storage capacitor **123**, and a silicon thin-film **422**, which serves as a source/drain channel region of the current-thin-film transistor **122**. Next, an insulation film **424**, which serves as a gate insulation film, is formed over the silicon thin-films **421**, **422**, and the first electrode **423**. Then, implantation of phosphorous (P) ions is selectively effected on the first electrode **423** to lower the resistance thereof. Next, as shown in FIG. 14(b), gate electrodes **111** and **111'**, which consist of TaN layers, are formed on the silicon thin-films **421** and **422** through the intermediation of the gate insulation film. Next, a resist mask **42** is formed on the silicon layer **422** serving as a current-thin-film transistor, and phosphorous (P) ions are implanted through self-alignment using the gate electrode as a mask to form an n-type source/drain region in the silicon layer **421**.

Subsequently, as shown in FIG. 14(c), a resist mask 412' is formed on the first silicon layer 421 and the first electrode, and boron (B) is ion-implanted in the silicon layer 422 through self-alignment using the gate electrode 111' as a mask to form a p-type source/drain region in the silicon layer 422. In this way, an n-channel type impurity doping 411 allows the switching thin-film transistor 121 to be formed. At this time, the current-thin-film transistor 122 is protected by the resist mask 42, so that the n-channel type impurity doping 411 is not performed. Then, a p-channel type impurity doping 412 allows the current-thin-film transistor 122 to be formed.

Further, though not illustrated, in a case in which a shift register of a drive circuit section which drives the switching transistor 121, and a thin-film transistor constituting a sample hold circuit etc., are to be formed on the same substrate, it is possible to form them simultaneously in the same step of process as has been described above.

A second electrode 425 of the storage capacitor may be formed together with the gate electrodes 111 and 111' simultaneously, either of the same or different materials.

As shown in FIG. 14(d), after the formation of an inter-layer insulation film 43 and, then, contact holes, electrode layers 426, 427, 428 and 429 formed of aluminum, ITO or the like are formed.

Next, after an inter-layer insulation film 44 is formed and flattened, contact holes are formed; then, ITO 45 is formed with a thickness of 1000 to 2000 angstroms, preferably about 1600 angstroms, in such a manner that one electrode of the current-thin-film transistor is connected thereto. For each pixel region, bank layers 46 and 47, which are not less than 2.0 μm in width, are defined. Next, an organic EL layer 48 is formed by an ink-jet method etc., in the region surrounded by the bank layers 46 and 47. After the organic EL layer 48 is formed, an aluminum-lithium layer with a thickness of 6000 to 8000 angstroms is deposited as an opposite electrode 49 on the organic EL layer 48. Between the organic EL layer 48 and the opposite electrode 49, a hole injection layer may be disposed, as shown in FIG. 6(a).

The process mentioned above enables an organic EL display device driven by means of a high-performance thin-film transistor to be formed. Since polysilicon is much higher in the mobility of carriers than amorphous-silicon, a rapid operation is possible.

In particular, in this embodiment, when the p-type current-thin-film transistor 122 and the n-type switching thin-film transistor 121 are formed, it is possible to form both of n-type and p-type thin-film transistors, which are complementary type thin-film transistors constituting a shift register of a drive circuit, a sample hold circuit and the like, being simultaneously formed in the above mentioned embodiment. The arrangement makes it possible to realize a construction capable of decreasing the deterioration with time of the current-thin-film transistor 122, without increasing the number of production steps.

As described above, in the first embodiment, an n-channel type current-thin-film transistor is used, and, in the second embodiment, a p-channel type current-thin-film transistor is used. Here, the deterioration with time of p-channel and n-channel type thin-film transistors will be examined.

FIG. 12 and FIG. 13 are charts showing respectively the deterioration with time of n-channel type and p-channel type thin-film transistors, especially of polysilicon thin-film transistors, under equivalent voltage application conditions. Numerals 511 and 512 of FIG. 12 indicate the conductivity characteristics of an n-channel type thin-film transistor, in the cases in which $V_d=4\text{V}$ and in which $V_d=8\text{V}$, respectively, before voltage application. Numerals 521 and 522 indicate

the conductivity characteristics of an n-channel type thin-film transistor, in the cases in which $V_g=0\text{V}$ and $V_d=15\text{V}$ and in which $V_d=4\text{V}$ and $V_d=8\text{V}$, respectively, after voltage application of approximately 1000 seconds. Numerals 811 and 812 of FIG. 13 indicate the conductivity characteristics of a p-channel type thin-film transistor in the cases in which $V_d=4\text{V}$, and in which $V_d=8\text{V}$, respectively, before voltage application. Numerals 821 and 822 indicate the conductivity characteristics of a p-channel type thin-film transistor in the cases in which $V_g=0\text{V}$ and $V_d=15\text{V}$, and in which $V_d=4\text{V}$ and $V_d=8\text{V}$, respectively, after voltage application for approximately 1000 seconds. It can be seen that in the p-channel type thin-film transistor, the decrease of ON-current and the increase of OFF-current are smaller than in the n-channel type.

Taking into consideration the difference in the deterioration-with-time characteristic between the p-type and the n-type thin-film transistors as shown in FIG. 12 and FIG. 13 respectively, at least either a switching thin-film transistor or a current-thin-film transistor is formed of a p-channel type thin-film transistor, especially a p-type polysilicon thin-film transistor, whereby the deterioration with time can be suppressed. Further, by forming the switching thin-film transistor as well as the current-thin-film transistor of a p-type thin-film transistor, it is possible to maintain the characteristics of the display device.

While an organic EL display device is used as the luminescent device in the embodiment described above, this should not be construed restrictively, yet, it is needless to say that an inorganic EL display device or other current-driven luminescent devices are also applicable.

Industrial Applicability

The display apparatus according to the present invention can be used as a display apparatus equipped with a current-driven luminescent device such as an organic EL display device or an inorganic EL display device, and a switching device to drive the luminescent device, such as a thin-film transistor.

What is claimed is:

1. A light-emitting device comprising:

- a data line;
- a scan line;
- a pixel electrode;
- a counter electrode;
- a light-emitting element disposed between the pixel electrode and the counter electrode; and
- a first transistor having a conduction state controlled by data signals supplied through the data line, the first transistor controlling a current level of a current that flows through the light emitting element,

the light-emitting device being configured such that:

the data signals include a first data signal that sets a gate voltage of a first gate of the first transistor to a first gate voltage, the first gate voltage turning on the first transistor; and

the data signals include a second data signal that sets the gate voltage of the first gate of the first transistor to a second gate voltage, the second gate voltage turning on the first transistor, and the second gate voltage being greater than the first gate voltage,

wherein the light-emitting element does not emit a light during a first period in which the first gate voltage is applied to the first gate, and

the light-emitting element emits a light during a second period in which the second gate voltage is applied to the first gate.

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2. The light-emitting device according to claim 1, the light-emitting element emitting a light when the current flows through the light-emitting element.

3. The light-emitting device according to claim 1, the light-emitting element including an organic electroluminescent layer.

4. The light emitting device according to claim 1, further comprising a second transistor that controls an electrical connection between the data line and the first gate.

5. The light emitting device according to claim 1, a threshold voltage of the light-emitting element being larger than a threshold voltage of the first transistor.

6. The light emitting device according to claim 1, the light-emitting element emitting a light when the direct current follows through the light-emitting element.

7. A light-emitting device comprising:

a data line;

a scan line;

a pixel electrode;

a counter electrode;

a light-emitting element disposed between the pixel electrode and the counter electrode;

a first transistor having a conduction state controlled by data signals supplied through the data line, the first transistor controlling a current level of a current that flows through the light emitting element; and

data driving means for driving the light emitting device by supplying data signals to the data line, the data signals including a first data signal and a second data signal, the first data signal adapted to set a gate voltage of a first gate of the first transistor in a first period to a first gate voltage that turns on the first transistor such that the light-emitting element does not emit a light during the first period, the second data signal adapted to set the gate voltage of the first gate of the first transistor in a second period to a second gate voltage that turns on the first transistor such that the light-emitting element emits a light during the

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second period, wherein the second gate voltage is greater than the first gate voltage.

8. The light-emitting device according to claim 7, the light-emitting element emitting a light when the current flows through the light-emitting element.

9. The light-emitting device according to claim 7, the light-emitting element including an organic electroluminescent layer.

10. The light emitting device according to claim 7, further comprising a second transistor that controls an electrical connection between the data line and the first gate.

11. The light emitting device according to claim 7, a threshold voltage of the light-emitting element being larger than a threshold voltage of the first transistor.

12. The light emitting device according to claim 7, wherein the light-emitting element emits a light when the direct current follows to the light-emitting element.

13. A method of operating a light-emitting device, the light emitting device having a data line, a scan line, a pixel electrode, a counter electrode, a light-emitting element disposed between the pixel electrode and the counter electrode, and a first transistor having a conduction state controlled by data signals supplied through the data line, the first transistor controlling a current level of a current that flows through the light emitting element, the method comprising:

supplying a first data signal to the data line adapted to set a gate voltage of a first gate of the first transistor in a first period to a first gate voltage that turns on the first transistor such that the light-emitting element does not emit a light during the first period; and

supplying a second data signal to the data line adapted to set the gate voltage of the first gate of the first transistor in a second period to a second gate voltage that turns on the first transistor such that the light-emitting element emits a light during the second period, wherein the second gate voltage is greater than the first gate voltage.

* * * * *

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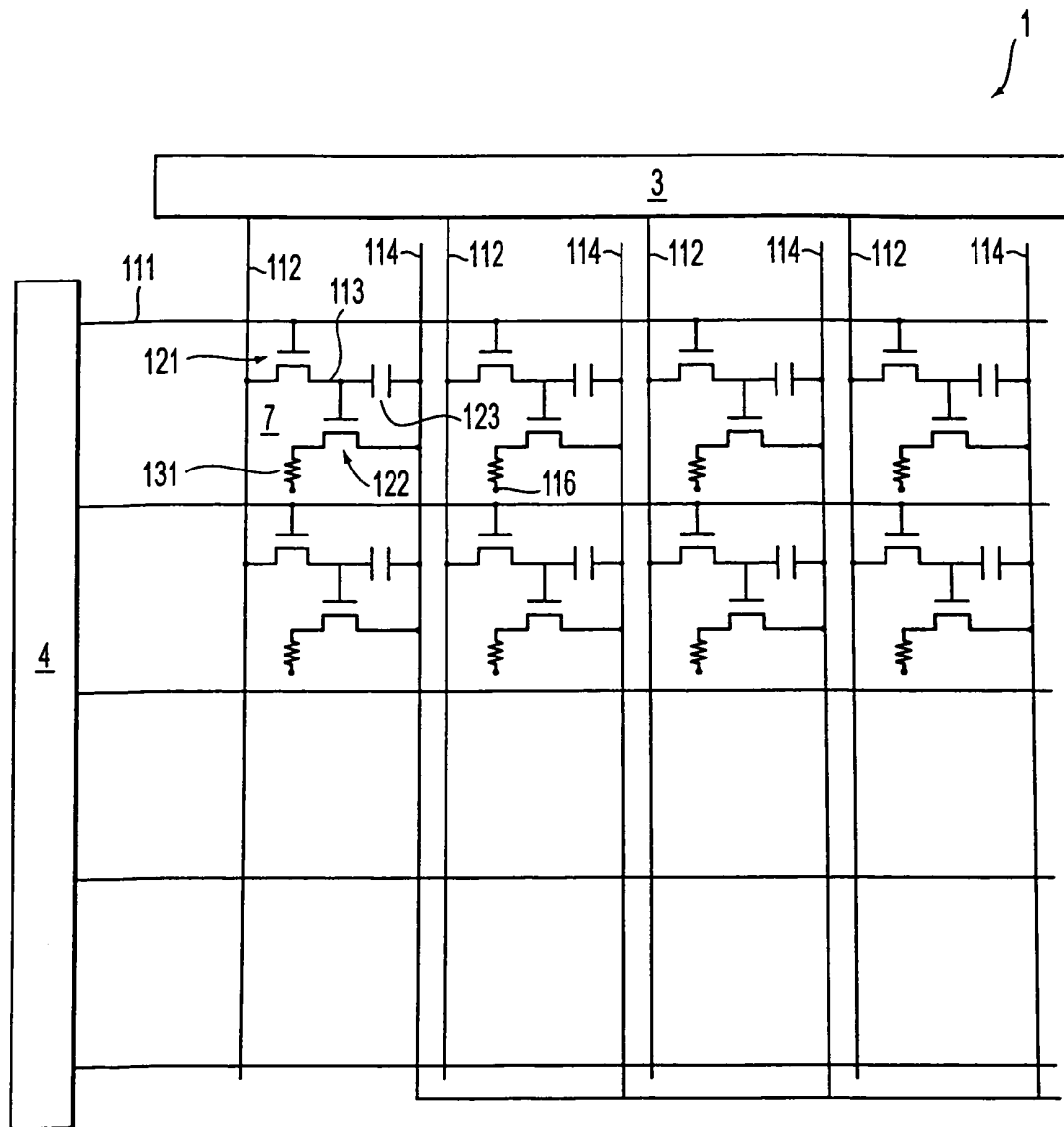


FIG. 1

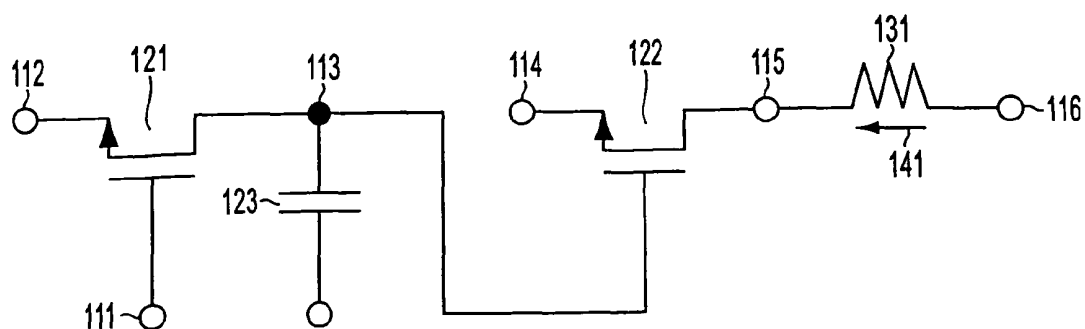


FIG. 2

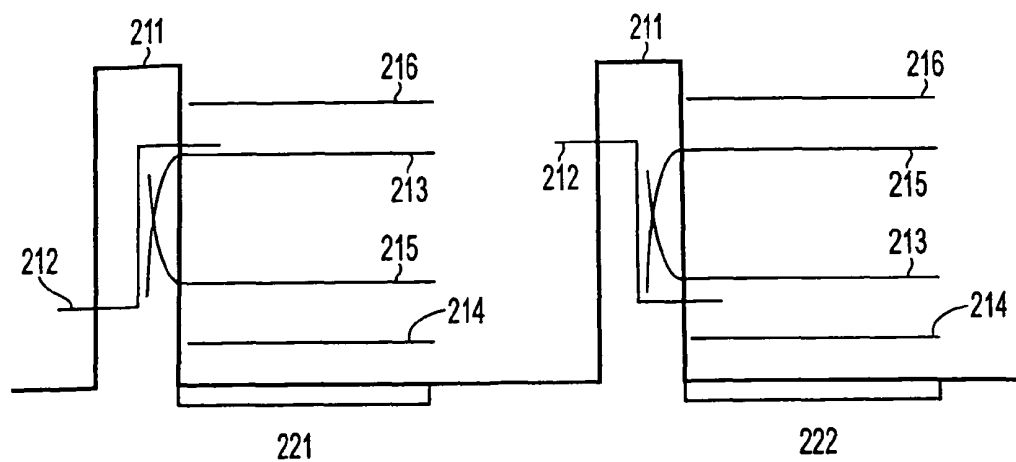


FIG. 3

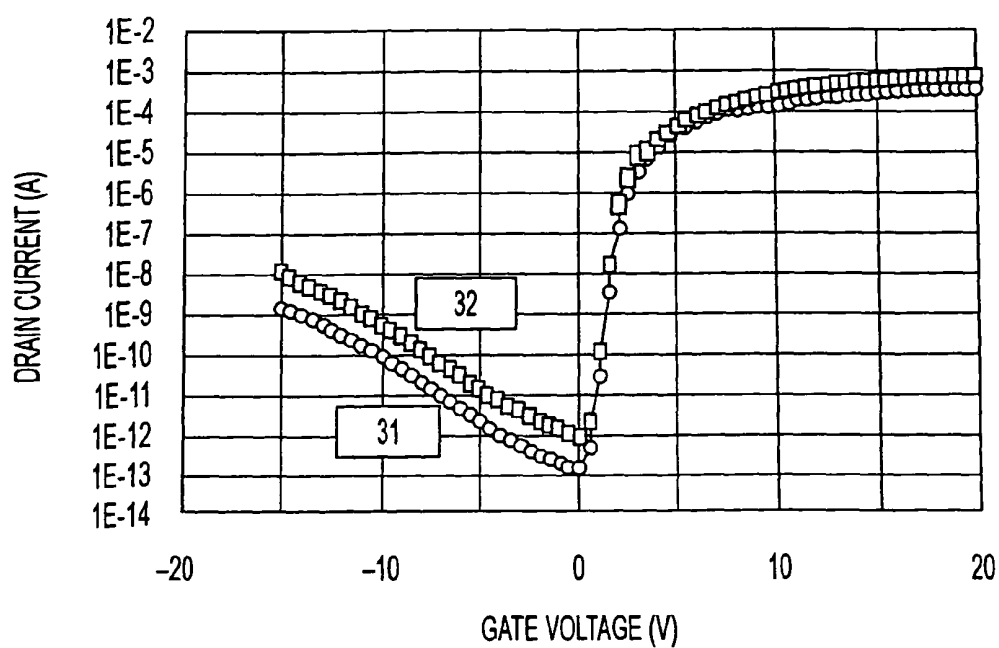
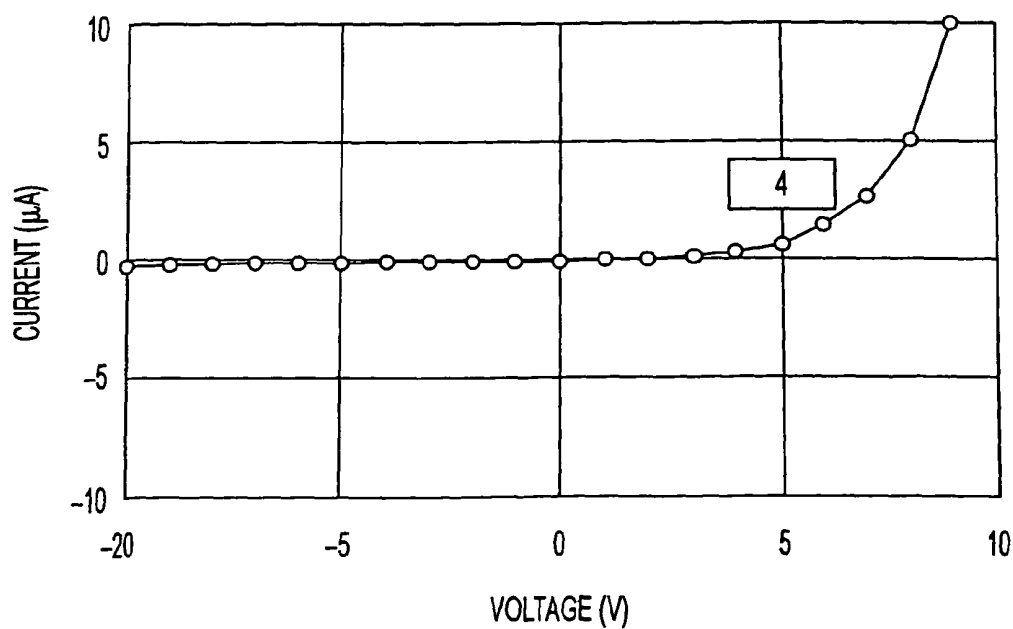
**FIG. 4****FIG. 5**

FIG. 6(a)

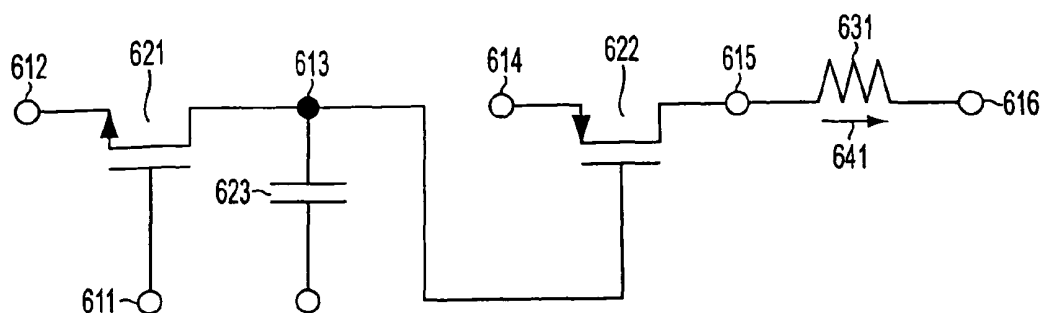


FIG. 7

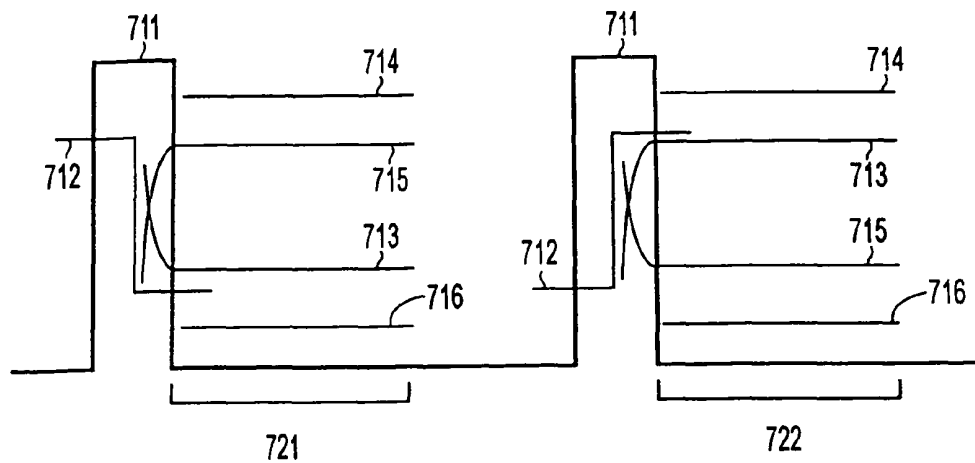


FIG. 8

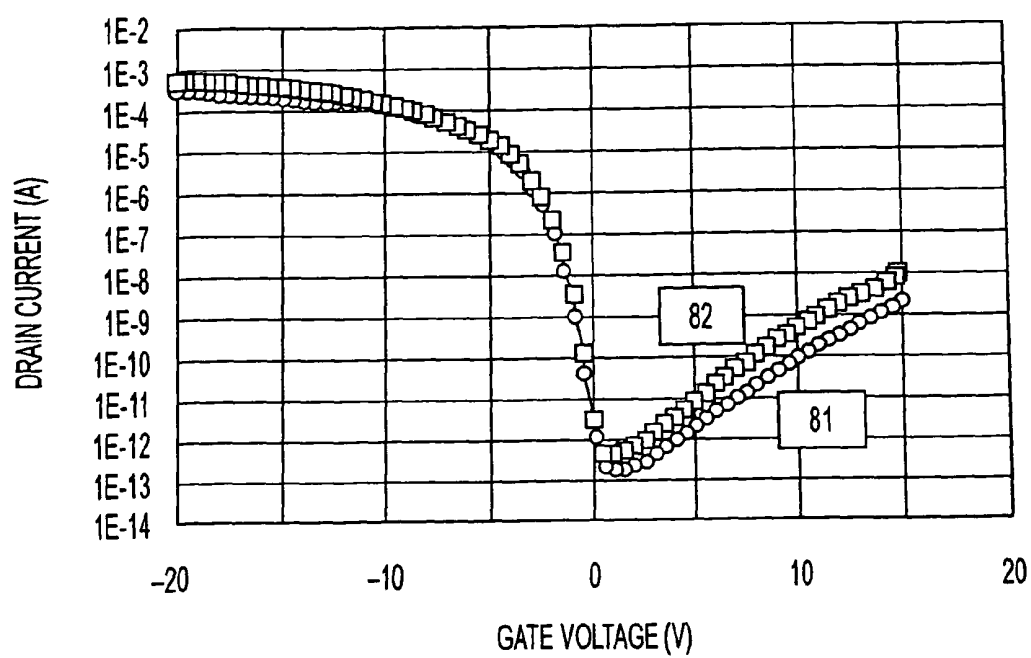
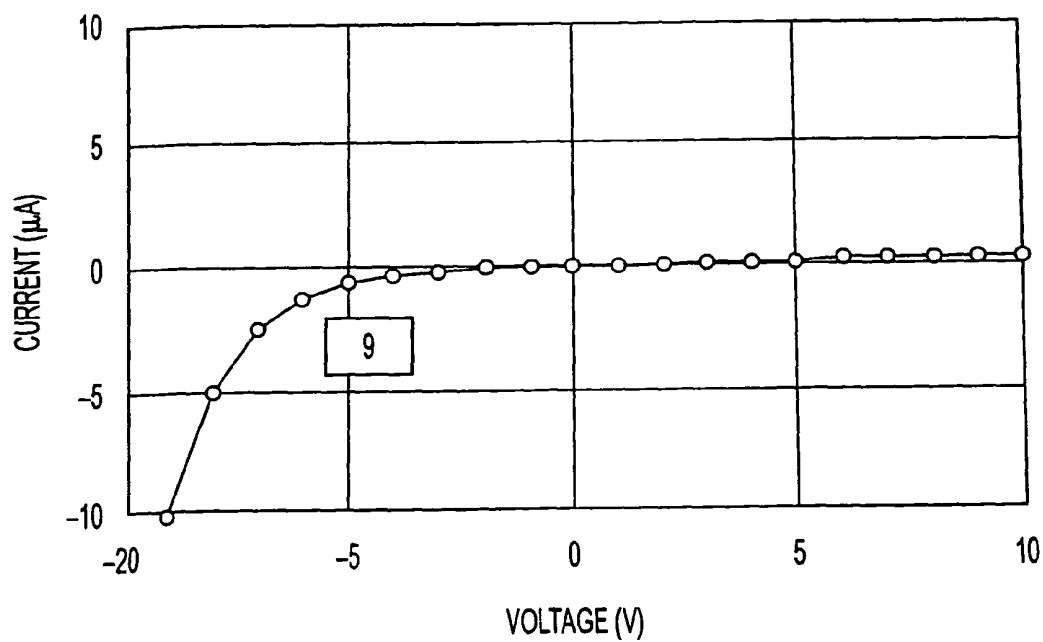
**FIG. 9****FIG. 10**

FIG. 11(a)

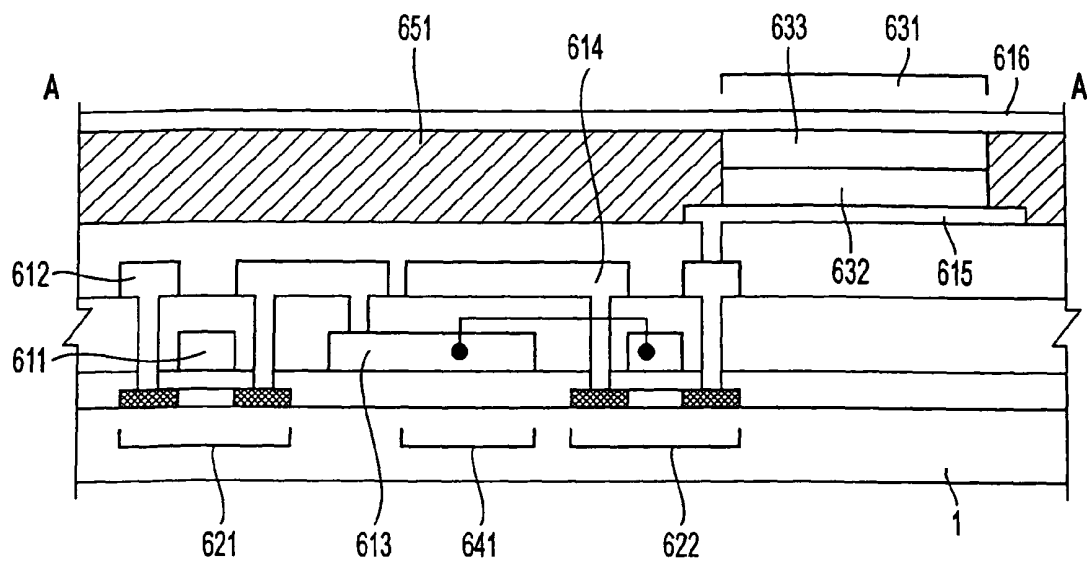
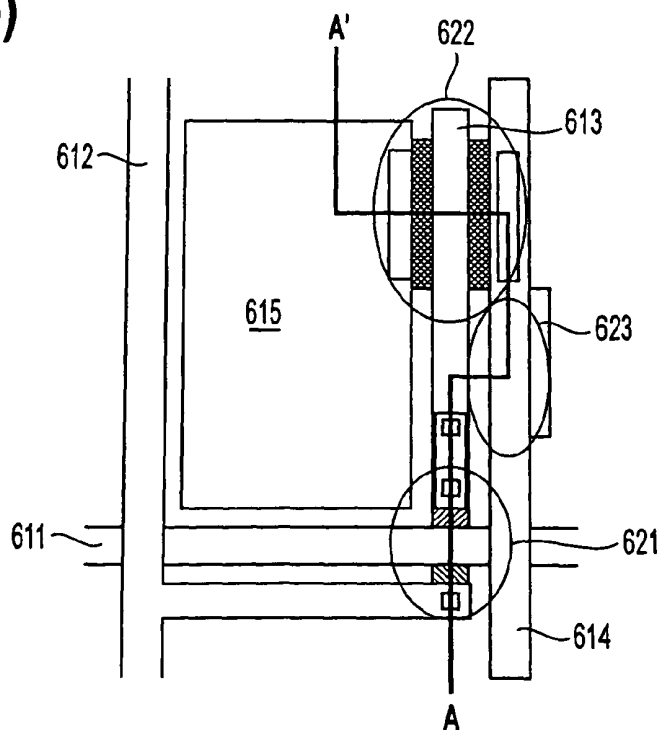


FIG. 11(b)



专利名称(译)	电流驱动的发光显示装置及其制造方法		
公开(公告)号	US8362489	公开(公告)日	2013-01-29
申请号	US12/289243	申请日	2008-10-23
[标]申请(专利权)人(译)	精工爱普生株式会社		
申请(专利权)人(译)	SEIKO EPSON CORPORATION		
当前申请(专利权)人(译)	SEIKO EPSON CORPORATION		
[标]发明人	KIMURA MUTSUMI ITOH TOMOYUKI		
发明人	KIMURA, MUTSUMI ITOH, TOMOYUKI		
IPC分类号	H01L27/14 G09F9/30 G09G3/32 H01L27/32 H01L51/50 H01L51/52 H05B33/08		
CPC分类号	G09G3/3225 H01L27/1255 H01L27/3248 H05B33/08 G09G3/3233 G09G3/3266 G09G3/3291 G09G2300/0417 G09G2300/0439 G09G2300/0819 G09G2300/0842 G09G2300/0866 G09G2300/0876 G09G2310/06 G09G2320/043 H01L27/3244 H01L51/5206 H01L51/5221 H01L2251/5315 Y02B20/325 H01L51/5234 Y02B20/32		
代理机构(译)	OLIFF & 贝里奇 , PLC		
优先权	1997032474 1997-02-17 JP 1997066046 1997-03-19 JP 09/155644 1998-10-02 US		
其他公开文献	US20090072758A1		
外部链接	Espacenet USPTO		

摘要(译)

公开了一种制造有机EL显示装置的方法。该显示装置包括基板，设置在基板上的晶体管，覆盖晶体管的平坦的层间绝缘膜，像素电极和有机EL层。

